

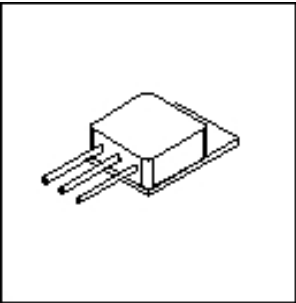
PPHZ52F120A (#24443)

RFQ/Sample

Insulated Gate Bipolar Transistor

Division	Lawrence	Datasheet	(none)
Mil-Spec	(none)		
Shipping	(none)	Qual Data	Contact Microsemi

Package



Maximum Electrical Rating	Symbol	Max	Unit
Breakdown Voltage Collector -to-Emitter	$B_{V(CES)}$	1200	V
Collector Current	I_C	52	A
Power Dissipation	P_D	300	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.4	°C/Watt

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Emitter Saturation Voltage					
($I_C=52$ A)	$V_{CE(sat)}$			3.2	V
Gate Threshold Voltage (min)	$V_{GE(th)}$		6.5	4.5	V
Input Capacitance Source -to-Drain Short	C_{ies}			1650	pF
Output Capacitance Gate -to-Source Short	C_{oes}			380	pF
Reverse Transfer Capacitance	C_{res}			160	pF
Gate to Emitter Charge	Q_{ge}			20	nC
[Q_{gc}]	Q_{gc}			75	nC
Total Gate Charge	$Q_{g(on)}$			160	nC
Turn-On Time	$t_{(on)}$			120	nsec
Turn-Off Time	$t_{(off)}$			465	nsec
Turn-Off Energy Loss	$E(off)$			2.4	mJ

